

ABSTRACT OF THE DISCLOSURE

Ru or Os is used for the main constituent of a mask film employed in patterning a capacitor electrode mainly made of Pt or Ir. As compared to the case of using a silicon oxide film for an etching mask for Pt or Ir, the thickness of a Ru film or Os film is only about one tenth that of the silicon oxide film. Thus, the aspect ratio of a patterning mask on Pt is as low as about 1 to 2. As a result, problems such as pattern collapse hardly arise.